# M1MA151WAT1, M1MA152WAT1

Preferred Device

# **Common Anode Silicon Dual Switching Diodes**

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC–59 package which is designed for low power surface mount applications.

#### Features

- Fast  $t_{rr}$ , < 10 ns
- Low C<sub>D</sub>, < 15 pF
- Pb–Free Packages are Available

#### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ )

Rating	Symbol	Value	Unit
Reverse Voltage M1MA151WAT M1MA152WAT	-	40 80	Vdc
Peak Reverse Voltage M1MA151WAT M1MA152WAT	-	40 80	Vdc
Forward Current Sing Du		100 150	mAdc
Peak Forward Current Sing Du		225 340	mAdc
Peak Forward Surge Current Sing Du		500 750	mAdc

#### THERMAL CHARACTERISTICS

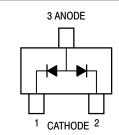
Rating	Symbol	Max	Unit
Power Dissipation	PD	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. t = 1 SEC



## **ON Semiconductor®**

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### MARKING DIAGRAM



 $\begin{array}{rl} Mx &= \text{Device Code} \\ x &= N \text{ for } 151 \\ O \text{ for } 152 \end{array}$ 

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping $^{\dagger}$
M1MA151WAT1	SC-59	3000/Tape & Reel
M1MA151WAT1G	SC-59 (Pb-Free)	3000/Tape & Reel
M1MA152WAT1	SC-59	3000/Tape & Reel
M1MA152WAT1G	SC–59 (Pb–Free)	3000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

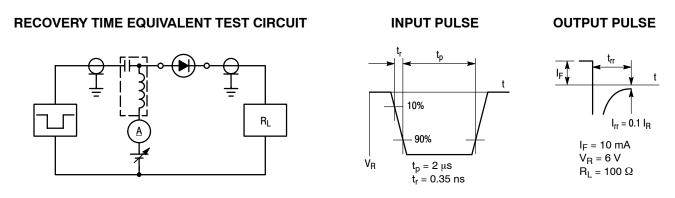
**Preferred** devices are recommended choices for future use and best overall value.

# M1MA151WAT1, M1MA152WAT1

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C)

Characteristic		Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	M1MA151WAT1 M1MA152WAT1	I <sub>R</sub>	V <sub>R</sub> = 35 V V <sub>R</sub> = 75 V	-	0.1	μAdc
Forward Voltage		V <sub>F</sub>	I <sub>F</sub> = 100 mA	-	1.2	Vdc
Reverse Breakdown Voltage	M1MA151WAT1 M1MA152WAT1	V <sub>R</sub>	I <sub>R</sub> = 100 μA	40 80	-	Vdc
Diode Capacitance		CD	V <sub>R</sub> = 0, f = 1.0 MHz	-	15	pF
Reverse Recovery Time (Figure 1)		t <sub>rr</sub> (Note 2)	$    I_F = 10 \text{ mA},  \text{V}_R = 6.0 \text{ V}, \\ \text{R}_L = 100 \ \Omega,  \text{I}_{\text{rr}} = 0.1  \text{I}_R $	-	10	ns

2. t<sub>rr</sub> Test Circuit





## M1MA151WAT1, M1MA152WAT1

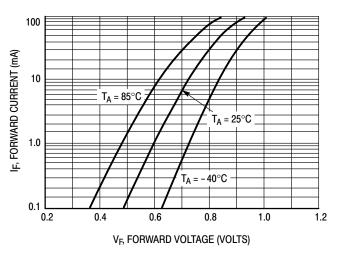


Figure 2. Forward Voltage

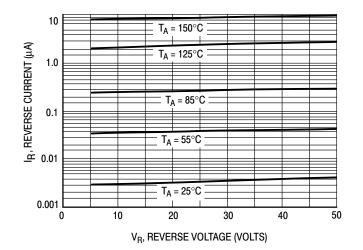


Figure 3. Leakage Current

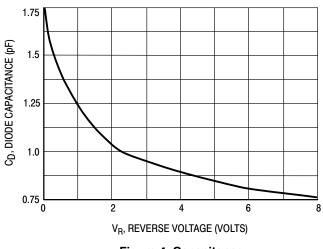


Figure 4. Capacitance

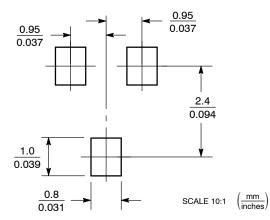




SCALE 2:1



#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SC-59 CASE 318D-04 ISSUE H

DATE 28 JUN 2012

NOTES:

DIES:
DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

#### GENERIC **MARKING DIAGRAM**



= Specific Device Code XXX Μ = Date Code

= Pb-Free Package\*

(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

Style 1:	STYLE 2:	STYLE 3:
PIN 1. Base	PIN 1. ANODE	PIN 1. ANODE
2. Emitter	2. N.C.	2. ANODE
3. Collector	3. CATHODE	3. CATHODE
Style 4:	Style 5:	STYLE 6:
Pin 1. Cathode	Pin 1. Cathode	PIN 1. ANODE
2. n.C.	2. Cathode	2. CATHODE
3. Anode	3. Anode	3. ANODE/CATHODE

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